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JFET



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## JFET



BITS Pilani, Dubai Campus



## JFET

#### Circuit analysis



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- □ When the V<sub>DD</sub>= $v_{DS}$  is small (positive) number, a small positive drain current results. The potential at drain  $v_D$  is approximately equal to source voltage  $v_S$  ( $v_S \approx v_D = 0$ )
- □ However if  $V_{GG}$  is increased, since  $v_{GS}$ = - $V_{GG}$ , then pn junction will become more reverse biased and depletion region gets wider.
- □ Because  $v_S (v_S \approx v_D = 0)$ , the depletion regions are symmetrical.
- When the VGG is sufficiently increased, the depletion region will be widened and channel will become narrower.
- □ The value of  $v_{GS}$ = -V<sub>GG</sub>, which eliminates the channel is called as <u>pinchoff</u> voltage.





As long as  $V_{DD} = v_{DS} = v_D v_S$  remains small, the depletion region will be essentially symmetrical and  $i_D$  will be proportional to  $v_{DS}$ , i. e channel will behave as a linear resistor.

However, if  $V_{DD} = v_{DS} = v_D \cdot v_S$  gets larger, then  $i_D$  gets larger and  $v_D$  becomes greater than  $v_S$ 



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- Since gate drain voltage is negative and gate source voltage is zero, portion of the pn junction between the gate and drain is more reverse biased than portion between gate and source.
- Due to this channel is narrower at the drain end than source end.





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- As v<sub>DS</sub> increases, i<sub>D</sub> also increases, channel gets narrower at the drain end than source end. The channel resistance increases and its nature is non linear.
- If v<sub>DS</sub> is made large enough pinch off is reached as shown

$$\Box v_{GD} = v_{GS} - v_{DS} = 0 - v_{DS} = V_p \text{ or } v_{DS} = -V_p$$





 $\Box$  For  $v_{DS} > -V_p$ , channel is still pinched off (very narrow), then the drain current will remain constant for  $v_{DS} \ge -V_{p}$ , and drain current is said to saturate. The plot for  $i_D$  vss  $v_{DS}$  is shown  $\Box$  For  $v_{GS}$ =0. The value of constant saturation current is  $I_{DSS}$ , it can range from tenths of mA to  $I_{DSS}$ hundred of mA. pn junction will breakdown if large Reverse voltage is applied.

 $BV_{DSS}$ 



## JFET

Pinch off can be reached in two ways

- 1. When  $v_{GS} = 0$  V, the channel is pinched off for  $v_{GD} = -v_{DS} = Vp$ or  $v_{DS} = -Vp$ .
- 2. When  $V_{GG} > 0$  or  $v_{GS} < 0$ , the channel is pinched off, when  $v_{GD} = v_{GS} v_{DS} = Vp$  or  $v_{DS} = v_{GS} Vp$
- Thus by decreasing vGS, the value of vDS required to pinch off the channel decreases.

# JFET (Drain characteristics)





# JFET (Drain characteristics)



- The dashed curve is corresponding to  $v_{DS} = v_{GS} Vp$
- To the right of this curve , ( $v_{DS} > v_{GS} Vp$ ), The channel is pinched off and this region is called as pinch off region or <u>saturation region</u>. (active region).
- To the left of this curve, ( $v_{DS} < v_{GS} Vp$ ), the *channel is not* pinched off and the region is called as <u>ohmic region</u>.
- When the gate is sufficiently reverse biased, channel will be totally eliminated for  $v_{GS} < Vp$ , under this circumstances increasing  $v_{DS}$ , will not be sufficient to produce a drain current.  $i_D=0$  and JFET is said to be in cutoff.



# JFET (Equations)

When the JFET is in the ohmic region, drain current iD is given by  $i_{D} = I_{DSS} \left[ 2 \left( 1 - \frac{v_{GS}}{V_{p}} \right) \frac{v_{DS}}{-V_{p}} - \left( \frac{v_{DS}}{V_{p}} \right)^{2} \right]$ 

For a small value of vDS, we have 
$$-Vp >> vDS$$
, so  $\left(\frac{v_{DS}}{V_p}\right)^2$  is small , thus

$$i_D = I_{DSS} \left[ 2 \left( 1 - \frac{v_{GS}}{V_p} \right) \frac{v_{DS}}{-V_p} \right] = \frac{2I_{DSS}}{-V_p} \left( 1 - \frac{v_{GS}}{V_p} \right) v_{DS}$$



# JFET (Equations)

From which we can write 
$$\frac{i_D}{v_{DS}} \approx \frac{2I_{DSS}}{-V_p} \left(1 - \frac{v_{GS}}{V_p}\right) = \frac{2I_{DSS}(v_{GS} - V_p)}{V_p^2}$$

Thus for a small  $v_{DS}$ , channel behaves as a linear resistor  $r_{DS}$  and is given by

$$r_{DS} = \frac{v_{DS}}{i_D} \approx \frac{V_p^2}{2I_{DSS}(v_{GS} - V_p)}$$

When the JFET is in the active region, drain current is

$$i_D = I_{DSS} \left( 1 - \frac{v_{GS}}{V_p} \right)^2$$





N-Channel DE-MOSFET Structure



- The resistance between reverse biased gate and source is typically in megaohms.
- For MOSFET, because of the insulation between gate and the substrate, the resistance between the gate and source is extremely high (in 10<sup>10</sup> to 10<sup>15</sup>)
- If v<sub>GS</sub> is made negative, the positive charges are induced on the n channel, there by effectively narrowing it.
- For varying value of vDS, the behavior of the device is similar to the JFET.
- Since it operates in the depletion mode, it is called as depletion MOSFET.







Assume that MOSFET is in active region, then

$$i_D = I_{DSS} \left( 1 - \frac{v_{GS}}{V_P} \right)^2 = 18mA$$
  
 $v_{DS} = -500 (18 \times 10^{-3}) + 16 = 7V$ 

Since 
$$v_{DS} = 7 > v_{GS} - V_p = 1 + 2 = 3V$$
,  
then the MOSFET is indeed in the  
active region



#### Notes on Operational Amplifiers (Op Amps).

Comments. The name Op Amp comes from "operational amplifier."

#### **Op Amp Golden Rules** (memorize these rules)

- 1) The op amp has infinite open-loop gain.
- The input impedance of the +/- inputs is infinite. (The inputs are ideal voltmeters). The output impedance is zero. (The output is an ideal voltage source.)
- No current flows into the +/- inputs of the op amp. This is really a restatement of golden rule 2.
- 4) In a circuit with negative feedback, the output of the op amp will try to adjust its output so that the voltage difference between the + and inputs is zero  $(V_+ = V_-)$ .

#### **IDEAL OP AMP BEHAVOIR.**

The relationship between the input ant the output of an ideal op amp (assumptions: infinite open loop gain, unlimited voltage).

for  $V_+ - V_- > 0$ :  $V_{out} \rightarrow +\infty$ for  $V_+ - V_- < 0$ :  $V_{out} \rightarrow -\infty$ for  $V_+ - V_- = 0$ :  $V_{out} = 0$ 

<u>Op Amp Schematic Symbol</u> (The upper input is usually the inverting input. Occasionally it is drawn with the non-inverting input on top when it makes the schematic easier to read. The position of the inputs may vary within the same schematic, so always look closely at the schematic! )



**Negative Feedback.** Most of the basic op amp building blocks rely on negative feedback. You can easily identify the type of feedback used by the op amp circuit. For negative feedback, the output is connected to the inverting input (– input). For positive feedback, the output is connected to the non-inverting input (+ input).

<u>The Input Impedance of the Circuit</u> is defined as the rate of change of  $V_{in}$  with respect to a change of  $I_{in}$ . This is simply the derivative  $\frac{dV_{in}}{dI_{in}}$ . The input impedance of the *circuit* is not in general the same as the impedance of the op amps inputs.

<u>The Output Impedance of the Circuit</u>, for the examples shown here, is the output impedance of the op amp. Output impedance is defined as the rate of change of  $V_{out}$  with respect to a change of  $I_{out}$ . This is simply the derivative  $\frac{dV_{out}}{dI_{out}}$ . For the ideal op amp, the output impedance is zero.

output impedance is zero.

#### **Basic Op Amp Building Blocks**

#### **Inverting Amplifier**



Analysis of the inverting amplifier starts with our op amp golden rules. From rule #4 we know that  $V_{-} = V_{+}$  and that  $V_{-} = 0$  because  $V_{+}$  is connected to ground. From rule #3 we know that  $I_{in} = I_{f}$  because no current flows into the inverting input.

$$V_{-} = V_{+}$$
  $V_{+} = 0$   $I_{in} = I_{f} = I$ 

Then we can find the relationship between  $V_{in}$  and  $V_{out}$  using Ohm's law (OL) and Kirchhoff's voltage law (KVL).

$$V_{in} - V_{-} = I_{in}R_{in} \qquad V_{in} - 0 = IR_{in} \qquad V_{in} = IR_{in} \qquad I = \frac{V_{in}}{R_{in}}$$
$$V_{-} - V_{out} = I_{f}R_{f} \qquad 0 - V_{out} = IR_{f} \qquad V_{out} = -IR_{f}$$
$$V_{out} = -\frac{R_{f}}{R_{in}}V_{in}$$

The voltage gain  $A_V$  is the derivative of  $V_{out}$  with respect to  $V_{in}$ . When the amplifier has only one input and  $V_{out} = 0$  when  $V_{in} = 0$ , we will make the assumption that  $A_V = V_{out}/V_{in}$ .

$$A_{v} = \frac{V_{out}}{V_{in}} = \frac{-IR_{f}}{IR_{in}} = -\frac{R_{f}}{R_{in}}$$

Alternatively we could have started our analysis from the voltage divider formed by  $R_{\rm f}$  and  $R_{\rm in}$ . The voltage divider will relate the voltage at  $V_{-}$  with  $V_{\rm out}$  and  $V_{\rm in}$ . In this case The total voltage across the divider is  $V_{\rm out} - V_{\rm in}$ . Because the bottom end of the divider is not connected to ground, we must add the extra  $V_{\rm in}$  term to offset  $V_{-}$ . We arrive at the same result.



The input impedance of the inverting amplifier is determined by  $R_{in}$ . Note that  $V_{-}$  is held at the same voltage as  $V_{+}$  by the op amp feedback. Because  $V_{+}$  is connected to ground, the input impedance is just  $R_{in}$ .

#### **Non-inverting Amplifier**



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$$V_{-} = V_{+}$$
  $V_{+} = V_{in}$   $I_{in} = I_{f} = I$ 

Then we can find the relationship between  $V_{in}$  and  $V_{out}$  using Ohm's law (OL) and Kirchhoff's voltage law (KVL).

$$-V_{-} = I_{1}R_{1} \qquad -V_{in} = IR_{1} \qquad I = -\frac{V_{in}}{R_{1}}$$
$$V_{-} - V_{out} = I_{f}R_{f} \qquad V_{in} - V_{out} = IR_{f} \qquad V_{out} = V_{in} - IR_{f}$$
$$V_{out} = V_{in} - \left(-\frac{V_{in}}{R_{1}}\right)R_{f} = V_{in}\left(1 + \frac{R_{f}}{R_{in}}\right)$$

The voltage gain  $A_V$  is the derivative of  $V_{out}$  with respect to  $V_{in}$ . When the amplifier has only one input and  $V_{out} = 0$  when  $V_{in} = 0$ , we will make the assumption that  $A_V = V_{out}/V_{in}$ .

$$A_{v} = \frac{V_{out}}{V_{in}} = \left(1 + \frac{R_{f}}{R_{in}}\right)$$

Alternatively we could have started out analysis from the voltage divider formed by  $R_{\rm f}$  and  $R_{\rm in}$ . The voltage divider will relate the voltage at  $V_{-}$  with  $V_{\rm out}$  and  $V_{\rm in}$ . In this case The total voltage across the divider is  $V_{\rm out}$  and the we know that  $V_{-} = V_{\rm in}$ . We arrive at the same result.



$$\begin{split} V_{-} &= V_{out} \left( \frac{R_1}{R_1 + R_f} \right) = V_{in} \\ V_{out} \left( \frac{R_1}{R_1 + R_f} \right) \left( \frac{R_1 + R_f}{R_1} \right) = V_{in} \left( \frac{R_1 + R_f}{R_1} \right) = V_{in} \left( 1 + \frac{R_f}{R_1} \right) \\ V_{out} &= V_{in} \left( 1 + \frac{R_f}{R_1} \right) \end{split}$$

The input impedance of the follower is the input impedance of the op amps input. For an ideal op amp the input impedance is infinite.





This is a special case of the non-inverting amplifier with  $R_{in} \rightarrow \infty$  and  $R_f = 0$ . The follower has a very high input impedance. Voltage follower has application when the source voltage can not supply very much current, a pH meter for example.

**Current-to-Voltage Converter** (AKA, I-V Converter, Transimpedance Amplifier). This circuit takes an input current and converts it to an output voltage. The input impedance of the ideal current to voltage converter is zero (the ideal current meter).



Analysis of the current-to-voltage converter starts with our op amp golden rules. From rule #4 we know that  $V_{-} = V_{+}$  and that  $V_{-} = 0$  because  $V_{+}$  is connected to ground. From rule #3 we know that  $I_{in} = I_{f}$  because no current flows into the inverting input.

$$V_{-} = V_{+}$$
  $V_{+} = 0$   $I_{in} = I_{f} = I$ 

Then we can find the relationship between  $V_{in}$  and  $V_{out}$  using Ohm's law (OL) and Kirchhoff's voltage law (KVL).

$$\begin{split} I_{in} &= I_f \\ V_- - V_{out} &= I_f R_f \qquad 0 - V_{out} = I_f R_f \qquad V_{out} = -I_f R_f \\ V_{out} &= -I_f R_f = -I_{in} R_f \end{split}$$

The current-to-voltage converter has transimpedance gain. Transimpedance gain is not unitless, it has units of impedance (Ohms). The transimpedance gain  $A_Z$  is the derivative

of  $V_{\text{out}}$  with respect to  $I_{\text{in}}$ . When the amplifier has only one input and  $V_{\text{out}} = 0$  when  $I_{\text{in}} = 0$ , we will make the assumption that  $A_{\text{V}} = V_{\text{out}}/I_{\text{in}}$ .

$$A_Z = \frac{V_{out}}{I_{in}} = \frac{-I_{in}R_f}{I_{in}} = -R_f$$

**Summing Amplifier.** This circuit will add (and subtract) the input voltages. Subtraction is accomplished by inverting the voltages before adding them. Note that summing can only occur for inputs to the inverting side of the op amp. This is because of the  $V_{-}$  node is a current summing junction where the input currents sum to the feedback current.



This is another look at the summing amplifier that emphases the summing junction.



Analysis of the summing amplifier starts with our op amp golden rules. From rule #4 we know that  $V_{-} = V_{+}$  and that  $V_{-} = 0$  because  $V_{+}$  is connected to ground. From rule #3 we know that  $\sum I_{inn} = I_{f}$  because no current flows into the inverting input. ( $I_{inn}$  is the current of the *n*th input.)

$$V_{-} = V_{+}$$
  $V_{+} = 0$   $\sum I_{inn} = I_{in1} + I_{in2} + I_{in3} = I_{f}$ 

Then we can find the relationship between  $V_{in}$  and  $V_{out}$  using Ohm's law (OL) and Kirchhoff's voltage law (KVL).

$$\begin{split} V_{inn} - V_{-} &= I_{inn} R_{inn} \qquad V_{inn} - 0 = I R_{inn} \qquad V_{inn} = I_{inn} R_{inn} \qquad I_{inn} = \frac{V_{inn}}{R_{inn}} \\ V_{-} - V_{out} &= I_{f} R_{f} \qquad 0 - V_{out} = I R_{f} \qquad V_{out} = -I_{f} R_{f} \\ V_{out} &= -I_{f} R_{f} = -R_{f} \left( I_{in1} + I_{in2} + I_{in3} \right) = -R_{f} \left( \frac{V_{in1}}{R_{in1}} + \frac{V_{in2}}{R_{in2}} + \frac{V_{in3}}{R_{in3}} \right) = -\frac{R_{f}}{R_{in1}} V_{in1} - \frac{R_{f}}{R_{in2}} V_{in2} - \frac{R_{f}}{R_{in3}} V_{in3} \\ V_{out} &= -\frac{R_{f}}{R_{in1}} V_{in1} - \frac{R_{f}}{R_{in2}} V_{in2} - \frac{R_{f}}{R_{in3}} V_{in3} \end{split}$$

The voltage gain  $A_V$  is the derivative of  $V_{out}$  with respect to  $V_{in}$ .

$$V_{out} = A_{V1}V_{in1} + A_{V2}V_{in2} + A_{V3}V_{in3} + \cdots$$
  
the gain of the *n*th input :  $A_{Vn} = \frac{dV_{out}}{dV_{inn}} = -\frac{R_f}{R_{inn}}$ 

**Differential Amplifier.** The term *differential* is used in the sense of *difference*. Do not confuse the differential amplifier with the differentiator. One important application of the differential amplifier over comes the problem of grounding that you encountered in lab when using the oscilloscope to make measurements. The typical oscilloscope always performs voltage measurements with respect to is own ground. A differential amplifier used before the scope input could measure the  $V_{\pm in}$  with respect to  $V_{-in}$ . The ground of the differential amplifier would be connected to the ground of the scope for this application, so the  $V_{out}$  will be measured correctly.



Analysis of the differential amplifier starts with our op amp golden rules. From rule #4 we know that  $V_{-} = V_{+}$ . From rule #3 we know that  $I_{1} = I_{2}$  and that  $I_{3} = I_{4}$  because no current flows into the inputs.

$$V_{-} = V_{+}$$
  $I_{1} = I_{2}$   $I_{3} = I_{4}$ 

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Then we can find the relationship between  $V_{\pm in}$ ,  $V_{-in}$ , and  $V_{out}$  using the voltage divider equations. We recognize that  $V_{-} = V_{+}$  and that  $V_{+}$  will be the output of the voltage divider formed by the two resistors connected to the non-inverting input. The voltage at  $V_{-}$  is the output of the voltage divider formed by the two resistors connected to the inverting input.



The voltage gain  $A_{\rm V}$  is the derivative of  $V_{\rm out}$  with respect to each input  $V_{\rm in}$ .

the gain for 
$$V_{+in}$$
:  $A_{V+in} = \frac{dV_{out}}{dV_{+in}} = +\frac{R_2}{R_1}$   
the gain for  $V_{-in}$ :  $A_{V-in} = \frac{dV_{out}}{dV_{-in}} = -\frac{R_2}{R_1}$ 

The inverting amplifier with generalized impedances. The results derived above can be extended to general impedances. Note that  $Z_f$  and  $Z_{in}$  can be the impedance of any network. The following are examples of the inverting amplifier, but ANY of the previous examples can be generalized in this way.





Integrator. A capacitor as the feedback impedance.



$$\begin{aligned} V_{out}(\omega) &= \frac{j}{\omega R_{in} C_f} V_{in}(\omega) \\ \left| V_{out}(\omega) \right| &= \frac{1}{\omega R_{in} C_f} V_{in}(\omega) \\ V_{out}(\omega) &= -\frac{1}{R_{in} C_f} \int V_{in}(\omega) \, \mathrm{d} \, t \\ A_V(\omega) &= \frac{V_{out}}{V_{in}} = \frac{j}{\omega R_{in} C_f} \\ \left| A_V(\omega) \right| &= \left| \frac{V_{out}}{V_{in}} \right| = \frac{1}{\omega R_{in} C_f} \\ \frac{\mathrm{d} \, V_{in}}{\mathrm{d} \, I_{in}} &= R_{in} \end{aligned}$$

Analysis of the integrator in the frequency domain is a simple extension of our generalized result for the inverting amplifier.

$$Z_{in} = R_{in} \qquad Z_f = \frac{1}{j\omega C_f} \qquad V_{out} = -\frac{Z_f}{Z_{in}}$$
$$V_{out} = -\frac{Z_f}{Z_{in}} V_{in} = -\frac{\frac{1}{j\omega C_f}}{R_{in}} V_{in} = -\frac{1}{j\omega R_{in} C_f} V_{in} = \frac{j}{\omega R_{in} C_f} V_{in}$$
$$A_V = \frac{V_{out}}{V_{in}} = \frac{j}{\omega R_{in} C_f}$$
$$|A_V| = \left|\frac{V_{out}}{V_{in}}\right| = \frac{1}{\omega R_{in} C_f}$$

**Time Domain Analysis of the Integrator** starts with our op amp golden rules. From rule #4 we know that  $V_{-} = V_{+}$  and that  $V_{-} = 0$  because  $V_{+}$  is connected to ground. From rule #3 we know that  $I_{in} = I_{f}$  because no current flows into the inverting input.

$$V_{-} = V_{+}$$
  $V_{+} = 0$   $I_{in} = I_{f} = I$ 

Then we can find the relationship between  $V_{in}$  and  $V_{out}$  using Ohm's law (OL) and Kirchhoff's voltage law (KVL).

$$\begin{split} V_{in} - V_{-} &= I_{in} R_{in} \qquad V_{in} - 0 = I R_{in} \qquad V_{in} = I R_{in} \qquad I = \frac{V_{in}}{R_{in}} \\ \frac{d}{dt} (V_{-} - V_{out}) &= \frac{I_{f}}{C_{f}} \qquad \frac{d}{dt} (0 - V_{out}) = \frac{I}{C_{f}} \qquad \frac{d}{dt} V_{out} = -\frac{I}{C_{f}} \qquad V_{out} = -\frac{1}{C_{f}} \int I \, dt \\ V_{out} &= -\frac{1}{C_{f}} \int I \, dt = -\frac{1}{C_{f}} \int \frac{V_{in}}{R_{in}} \, dt = -\frac{1}{R_{in}C_{f}} \int V_{in} \, dt \\ V_{out} &= -\frac{1}{R_{in}C_{f}} \int V_{in} \, dt \end{split}$$

**Differentiator.** A capacitor as the input impedance.



 $\begin{aligned} V_{out}(\omega) &= -j\omega R_f C_{in} V_{in}(\omega) \\ \left| V_{out}(\omega) \right| &= -\omega R_f C_{in} V_{in}(\omega) \\ V_{out}(t) &= -R_f C_{in} \frac{\mathrm{d} V_{in}(t)}{\mathrm{d} t} \\ A_V(\omega) &= \frac{V_{out}}{V_{in}} = -j\omega R_f C_{in} \\ \left| A_V(\omega) \right| &= \left| \frac{V_{out}}{V_{in}} \right| = -\omega R_f C_{in} \\ \frac{\mathrm{d} V_{in}}{\mathrm{d} I_{in}} &= \frac{1}{j\omega C_{in}} \end{aligned}$ 

Analysis of the differentiator in the frequency domain is a simple extension of our generalized result for the inverting amplifier.

$$Z_{in} = \frac{1}{j\omega C_{in}} \qquad Z_f = R_f \qquad V_{out} = -\frac{Z_f}{Z_{in}}$$
$$V_{out} = -\frac{Z_f}{Z_{in}} V_{in} = -\frac{R_f}{\frac{1}{j\omega C_{in}}} V_{in} = -j\omega R_f C_{in} V_{in}$$
$$|V_{out}| = \omega R_f C_{in} V_{in}$$
$$A_V = \frac{V_{out}}{V_{in}} = -j\omega R_f C_{in}$$

$$\left|A_{V}\right| = \left|\frac{V_{out}}{V_{in}}\right| = \omega R_{f} C_{in}$$

**Time Domain Analysis of the Differentiator** starts with our op amp golden rules. From rule #4 we know that  $V_{-} = V_{+}$  and that  $V_{-} = 0$  because  $V_{+}$  is connected to ground. From rule #3 we know that  $I_{in} = I_{f}$  because no current flows into the inverting input.

$$V_{-} = V_{+}$$
  $V_{+} = 0$   $I_{in} = I_{f} = I$ 

Then we can find the relationship between  $V_{in}$  and  $V_{out}$  using Ohm's law (OL) and Kirchhoff's voltage law (KVL).

$$\frac{\mathrm{d}}{\mathrm{d}t} (V_{in} - V_{-}) = \frac{I_{in}}{C_{in}} \qquad \frac{\mathrm{d}}{\mathrm{d}t} V_{in} = \frac{I}{C_{in}} \qquad C_{in} \frac{\mathrm{d}}{\mathrm{d}t} V_{in} = I$$

$$V_{-} - V_{out} = I_{f} R_{f} \qquad 0 - V_{out} = I R_{f} \qquad V_{out} = -I R_{f}$$

$$V_{out} = -\left(C_{in} \frac{\mathrm{d}}{\mathrm{d}t} V_{out}\right) R_{f} = -R_{f} C_{in} \frac{\mathrm{d}}{\mathrm{d}t} V_{in}$$

$$V_{out} = -R_{f} C_{in} \frac{\mathrm{d}}{\mathrm{d}t} V_{in}$$

#### **Bipolar Junction Transistor (BJT**)

- Beside diodes, the most popular semiconductor devices is transistors. Eg: Bipolar Junction Transistor (BJT)
- Few most important applications of transistor are: as an amplifier as an oscillator and as a switch
- Amplification can make weak signal strong in general, provide function called Gain
- BJT is bipolar because both holes (+) and electrons (-) will take part in the current flow through the device
  - N-type regions contains free electrons (negative carriers)
  - P-type regions contains free holes (positive carriers)

### **Bipolar Junction Transistor (BJT**)

npnTransistor



pnpTransistor



a 3 terminal device. namely- emitter, base and collector

> npn transistor: emitter & collector are n-doped and base is p-doped.

heavily doped, collector is moderately doped and base is lightly doped and base is very thin. i.e.  $N_{DE} >> N_{DC} >> N_{AB}$ 

#### Mode of operation for BJT

Mode	V <sub>BE</sub>	V <sub>BC</sub>	
Forward active	Forward bias	<b>Reverse Bias</b>	
Reverse active	<b>Reverse Bias</b>	Forward Bias	
Saturation	Forward bias	ward bias Forward bias	
Cut off	<b>Reverse Bias</b>	<b>Reverse Bias</b>	

> Forward active region is widely used and Reverse active region is rarely used.

### **Different configuration of BJT**

### **Common base configuration**





Non-inverting voltage amplifier circuit

**Common emitter configuration** 

#### **Common collector configuration**



This type of configuration is commonly known as a **Voltage Follower** or **Emitter Follower** circuit.

#### Summary of BJT characteristics for different configuration

Characteristic	Common Base	Common Emitter	Common Collector
Input impedance	Low	Medium	High
Output impedance	Very High	High	Low
Phase Angle	<b>0</b> °	180°	0°
Voltage Gain	High	Medium	Low
Current Gain	Low	Medium	High
Power Gain	Low	Very High	Medium

➤The CB mode is generally only used in single stage amplifier circuits such as microphone pre-amplifier or RF radio amplifiers due to its very good high frequency response.

> The Emitter follower configuration is very useful for impedance matching applications because of the very high input impedance, in the region of hundreds of thousands of Ohms, and it has relatively low output impedance.



• For npn BJT in forward active mode:

$$V_{BE} > 0$$
 and  $V_{BC} < 0$ 

#### **Energy band diagram for npn BJT**





Reference: From L.C.G. Lesurf's (University of St. Andrews) The Scot's Guide to Electronics



➤1. Forward bias of EBJ causes electrons to diffuse from emitter into base.
➤ 2. As base region is very thin, the majority of these electrons diffuse to the edge of the depletion region of CBJ, and then are swept to the collector by the electric field of the reverse-biased CBJ.

> 3. A small fraction of these electrons recombine with the holes in base region.

> 4. Holes are injected from base to emitter region. (4) << (1).

> The two-carrier flow from [(1) and (4)] forms the emitter current ( $I_E$ ).

### **Collector current**

Collector-base diode is reverse biased therefore  $V_{CB} > 0$ 

$$I_{C} = I_{s} \left[ e^{\left(\frac{eV_{BE}}{kT} - 1\right)} \right] \quad \text{where} \qquad I_{s} = \frac{qA_{e}D_{n}n_{po}}{W} = \frac{qA_{e}D_{n}n_{i}^{2}}{N_{A}W}$$

- A<sub>e</sub> Area of base-emitter junction
- W Width of base region
- N<sub>A</sub> Doping concentration in base
- D<sub>n</sub> Electron diffusion constant

 $n_i$  Intrinsic carrier concentration = f(T)

#### **Base current**

- > Base current consists of two components:  $i_{B1}$  and  $i_{B2}$ :
- ↔  $i_{B1}$ , due to forward bias of EBJ, is an exponential function of  $V_{BE}$ .
- $\clubsuit$   $i_{\rm B2}$  , due to recombination, is directly proportional to the numbers of
- electrons injected from the emitter, which in turn is an exponential function of  $V_{BE}$ .

#### $\mathbf{I}_{\mathbf{C}}$ is independent of collector voltage

#### Forward Active Mode common base current gain (α)

In common base configuration, the current transfer mode ratio ( $\alpha$ ) of a bipolar transistor in the forward active mode is defined as the ratio of the collector current ( $I_C$ ) to the emitter current ( $I_E$ ):

$$\alpha = \frac{I_C}{I_E} \qquad \qquad I_E = I_C + I_B$$

#### Forward Active Mode common emitter current gain (β)

The current gain ( $\beta$ ) of a bipolar transistor under common emitter forward active mode is defined as the ratio of the collector current ( $I_C$ ) to the base current ( $I_B$ ):

$$\beta = \frac{I_C}{I_B}$$

$$\frac{I_E}{I_C} = 1 + \frac{I_B}{I_C} \qquad \frac{1}{\alpha} = 1 + \frac{1}{\beta} \qquad \beta = \frac{\alpha}{1 - \alpha}$$

### I-V Characteristics of npn BJT under forward active mode



> Input characteristics are like a normal forward biased diode. As  $V_{CB}$  increased  $I_E$  also increased due to Early Effect (increased reverse biased at CB junction causes reduction in effective base width).

► As the CB junction is reverse biased, the current  $I_C$  depends totally on  $I_E$ . When  $I_E=0$ ,  $I_C=I_{CB0}$  is the current caused by the minority carriers crossing the pn-junction.  $I_{cB0}$  is leakage current called as collector base current with emitter open. When  $I_E$  is increased,  $I_C$  is increased correspondingly.  $I_C = \alpha I_E + I_{CB0}$